

SUBSTRATE PROCESSING METHOD AND SUBSTRATE PROCESSING APPARATUS

ABSTRACT

A substrate processing method comprising: providing a substrate having a silicon-containing dielectric film in the substrate support; and generating plasma from a processing gas including a hydrogen- and fluorine-containing gas to etch the silicon-containing dielectric film, wherein the etching step comprises supplying the processing gas into the chamber, supplying a first radio-frequency signal for generating the plasma to the substrate support or the upper electrode, and supplying a first electrical bias to the upper electrode.

Fig. 3